

Introduction

The current transport through devices consisting of layers with quantum dots has attracted considerable interest for the semiconductor technology.

With decreasing dot size single electron/hole tunneling effects become visible leading to **single peaks** in the $I(V)$ characteristic.

In the following the **current instabilities** in a resonant tunneling **Quantum Dot Structure** will be studied with a master equation approach. The structure is embedded in an **external circuit**. Due to the strong negative differential conductance several fixed points exist and the performance of the device is crucially dependent on the chosen parameters.

The **bifurcation analysis** is done using linear stability analysis for the QD system.

A **global bifurcation** is found with numerical integration.

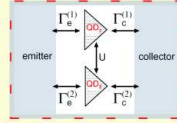
Differential equations

$$(I-V) \quad \frac{d}{dt} P = \underline{M}(V)P$$

$$(V) \quad C \frac{d}{dt} V = \frac{V_0 - V}{R} - (I(P, V))$$

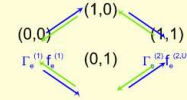
$$(I) = \frac{1}{2} \sum_{\nu} [j_{\nu} P + j_{\nu}^* P^*]$$

Model of the QD System



- QD system: two Quantum dots embedded between an emitter and a collector contact
- each QD has one discrete energy level ϵ_i
- U ... Xoulomb charging energy
- $\Gamma_e^{(i)}$... electron transition rate
- $f_e^{(i)}$... Fermi function at the emitter contact

Configuration Space (QD₁, QD₂)



→ electron enters the QD system
→ electron leaves the QD system

Master Equation

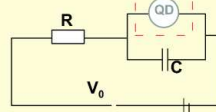
$$\dot{P} = \underline{M}P \quad \text{with} \quad P = (P_{00}, P_{10}, P_{01}, P_{11})^T$$

$$\underline{M} = \begin{pmatrix} -\Gamma_e^{(1)} f_e^{(1)} - \Gamma_c^{(2)} f_c^{(2)} & \Gamma_e^{(1)} (1 - f_e^{(1)}) + \Gamma_c^{(1)} & 0 & 0 \\ \Gamma_e^{(1)} f_e^{(1)} & -\Gamma_e^{(1)} (1 - f_e^{(1)}) - \Gamma_c^{(1)} - \Gamma_c^{(2)} f_c^{(2)} & \Gamma_c^{(2)} (1 - f_c^{(2)}) + \Gamma_e^{(2)} & 0 \\ \Gamma_c^{(2)} f_c^{(2)} & 0 & 0 & \Gamma_c^{(2)} (1 - f_c^{(2)}) + \Gamma_e^{(2)} \\ 0 & \Gamma_c^{(2)} (1 - f_c^{(2)}) & \Gamma_e^{(2)} f_e^{(2)} & -\Gamma_e^{(2)} (1 - f_e^{(2)}) - \Gamma_c^{(2)} \end{pmatrix}$$

with $\epsilon_1 = \epsilon_2 = U$
 $\Gamma_e^{(1)} = \Gamma_c^{(1)} = \Gamma_e^{(2)}$
 $\Gamma_c^{(2)} = 0.01 \cdot \Gamma_e^{(2)}$
 $U = k_B T / 0.03 \approx 2.87 m_e V$

- master equation describes the temporal evolution of the occupation probabilities P_i combined to the vector P
- matrix M contains all gain and loss processes scotched above

Electronic Circuit



- external circuit ensures a **global coupling**
- additional dynamic variable **U**
- capacity C and resistance R are easily changeable parameters

Dynamics of the System (I-V) will be analysed for different parameters **R** and **C**.

Current propagator

$$\underline{j}_c = \epsilon \begin{pmatrix} 0 & \Gamma_c^{(1)} & \Gamma_c^{(2)} & 0 \\ 0 & 0 & 0 & \Gamma_c^{(1)} \\ 0 & 0 & 0 & \Gamma_c^{(2)} \\ 0 & 0 & 0 & 0 \end{pmatrix}$$

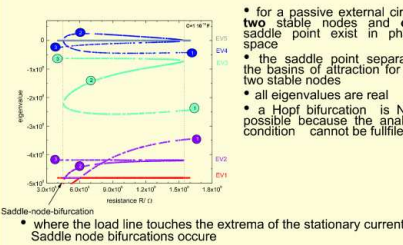
Collector

$$\underline{j}_e = \epsilon \begin{pmatrix} 0 & -\Gamma_e^{(1)} (1 - f_e^{(1)}) & -\Gamma_e^{(2)} (1 - f_e^{(2)}) & 0 \\ \Gamma_e^{(1)} f_e^{(1)} & 0 & 0 & -\Gamma_e^{(1)} (1 - f_e^{(1)}) \\ 0 & 0 & 0 & -\Gamma_e^{(2)} (1 - f_e^{(2)}) \\ 0 & \Gamma_e^{(1)} f_e^{(1)} & \Gamma_e^{(2)} f_e^{(2)} & 0 \end{pmatrix}$$

Emitter

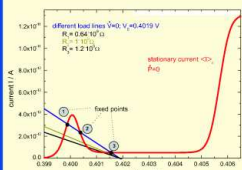
Resistance R

Passive external circuit (R, C positive)



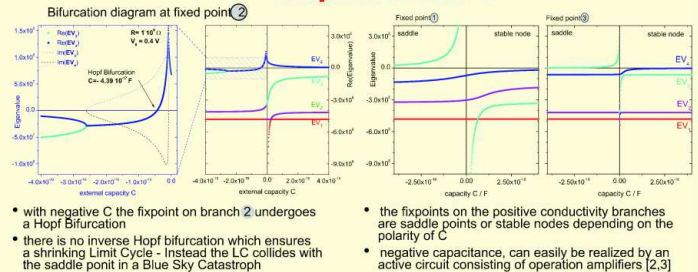
- for a passive external circuit **two stable nodes** and **one saddle point** exist in phase space
- the saddle point separates the basins of attraction for the two stable nodes
- all eigenvalues are real
- a Hopf bifurcation is NOT possible because the analytic condition cannot be fulfilled

Stationary solutions



- relaxation time of the circuit, RC is chose to be of the order of the transition rates $1/\Gamma$
- three fixed points for $V_0 \sim 0.4019$ V and $R = 4.10^7 \dots 1.61 \cdot 10^10 \Omega$

Capacitance C



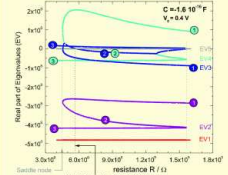
- with negative C the fixpoint on branch 2 undergoes a Hopf Bifurcation
- there is no inverse Hopf bifurcation which ensures a shrinking Limit Cycle - Instead the LC collides with the saddle point in a Blue Sky Catastroph
- the fixpoints on the positive conductivity branches are saddle points or stable nodes depending on the polarity of C
- negative capacitance, can easily be realized by an active circuit consisting of operation amplifiers [2,3]

Possible Applications

- fast **switching** of the device could be achieved by either varying the external voltage V_0 or the series resistance R

Active External circuit (C negative)

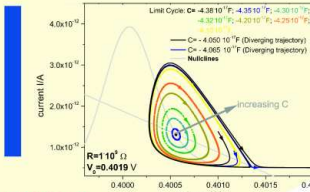
Bifurcation diagram



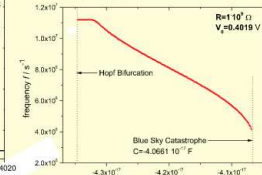
- for an active external circuit the two fixed points on the positive conductivity branches 1 & 3 are saddle points while the fixpoint in the middle 2 undergoes a Hopf bifurcation
- eigenvalues are real except two eigenvalues of the middle branch 2
- Saddle node bifurcations at $R = 4.55 \cdot 10^7 \Omega$ and $R = 1.56 \cdot 10^9 \Omega$

Blue Sky Catastrophe-Global Bifurcation

Transients in Phase Space

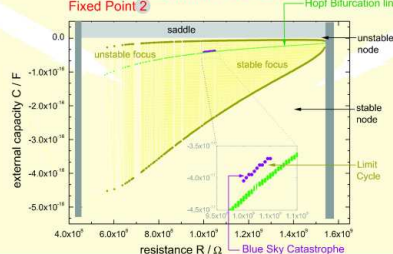


Frequency at the bifurcation Point



- the frequency stays constant at the Hopf bifurcation while it goes to zero (minute period) at the global homoclinic bifurcation
- after the LC has touched the saddle point (blue sky catastrophe) there is no stable fixed point in the system

Bifurcation diagram in R-C Space

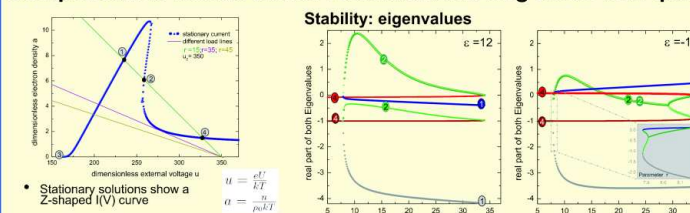


- following the Hopf bifurcation through the parameter space (R, C) one obtains the green line that shows the transition from the stable focus to the LC and an unstable focus
- in the shaded areas the eigenvalues are all real
- the limit cycle vanishes at the homoclinic bifurcation which is exemplary shown for R appr. $1 \cdot 10^9 \Omega$ with the violet dots

References

- [1] Kießlich, G., Wacker, A. and Schöll, Physica B 314, 459-463 (2002)
- [2] National Semiconductor Application Note 31, February 1978, Op Amp Circuit Collection
- [3] Martin A. D., Lerch M. L. F., Simmonds P. E., and Eaves L., Appl. Phys. Lett. 64, 1248 (1994)
- [4] Schöll, E., Amann, A., Rudolf, M. and Unkelbach, Physica B 314, 113-117 (2002)

Comparison to double barrier resonant tunneling diode with quantum well



- Parameter: $F = R^2 \rho_0 L_x L_y$ stance
- $a = \frac{R^2 \rho_0 L_x L_y}{\tau_{tr}}$
- $L = \frac{R^2 \rho_0 L_x L_y}{\tau_{tr}}$
- $q = \frac{RC}{\tau_{tr}}$
- $p = \frac{RC}{\tau_{tr}}$
- τ_s

• Comparing the performance of both systems some similarities but also some essential differences can be found. The Z-shape of the DBRT $I(V)$ curve has a bistability range leading to an inverse Hopf bifurcation. This ensures the existence of at least one stable fixed point.

Summary

For $C > 0$ we show that oscillatory instabilities caused by a Hopf bifurcation exist. There is a **range of C** on the negative conductivity branch that **separates the basins of attraction** for the two stable nodes.

Thus, the resonant tunneling QD structure could be used as a fast switching device

For $C < 0$ there is a Hopf bifurcation leading to uniform limit cycle oscillations. With increasing absolute value of C the oscillation amplitude increases while its shape transforms from an elliptic to a strongly nonlinear relaxation-type shape. At a certain value of C the limit cycle collides with the saddle-point on the low current branch and disappears. This represents a global homoclinic bifurcation.

Comparing the performance with a conventional double barrier resonant tunneling diode (DBRT) using a quantum well [4] we find that for the N-shape of the QD $I(V)$ no inverse Hopf bifurcation exists but parameter sets without stable fixed points.

Acknowledgement

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